

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

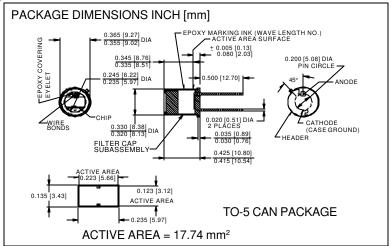






PHOTONIC Silicon Photodiode, Filter Combination Photovoltaic **DETECTORS INC.** 550 nm (green color) Type PDV-V404





FEATURES

- 550 nm CWL
- 70 nm FWHM
- · Large active area

DESCRIPTION: The **PDV-V404** is a silicon,

PIN planar diffused, photodiode with a green color 550 nm ⁺/-2 nm CWL wide band interferance filter and a wide 70 nm half bandwidth. Ideal for photometry & radiometry measurment applications.

APPLICATIONS

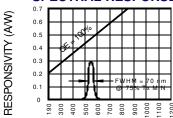
- Green color matching
- Color meters
- Film processing

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER MIN		MAX	UNITS
V_{BR}	Reverse Voltage		100	V
T _{STG}	Storage Temperature	-20	+85	°C
То	Operating Temperature Range	-15	+70	°C
Ts	Soldering Temperature*		+240	°C
I	Light Current		0.5	mA

^{*1/16} inch from case for 3 secs max

SPECTRAL RESPONSE



WAVELENGTH (nm)

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
lsc	Short Circuit Current***	H = 100 fc, 2850 K	150	200		μΑ
ΙD	Dark Current	H = 0, V _R = 10 mV		10	50	рА
RsH	Shunt Resistance	H = 0, V _R = 10 mV	.20	2		GΩ
TC RsH	Rsн Temp. Coefficient	H = 0, V _R = 10 mV		-8		%/℃
Cı	Junction Capacitance	H = 0, V _R = 10 V**		1700		pF
CWL	Center Wavelength	(CWL, λ o) +/- 2 nm		550		nm
HBW	Half Bandwidth	(FWHM)		70		nm
V _{BR}	Breakdown Voltage	I = 10 µuA	50	75		V
N EP	Noise Equivalent Power	V _R = 10 mV @ Peak		9x10 ⁻¹⁵		W/ V Hz
tr	Response Time	RL = 1 KΩ V _R = 10 V		1.0		μS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.**f = 1 MHz, ***without filter [FORM NO. 100-PDV-V404 REV A]